Small Signal Diodes
MMBD1401, MMBD1403, MMBD1404, MMBD1405

SOT−23
CASE 318BM

SOT−23
CASE 318−08

ABSOLUTE MAXIMUM RATINGS

(T_A = 25°C unless otherwise noted) (Notes 1, 2)

Rating	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	200	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA

Non−Repetitive Peak Forward Surge Current
   Pulse Width = 1.0 second
   Pulse Width = 1.0 microsecond
	I_{FSM}	
		
		1.0
		2.0
			A

Storage Temperature Range	T_{STG}	−55 to +150	°C
Operating Junction Temperature	T_J	150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. These ratings are based on a maximum junction temperature of 150°C.
2. These are steady−state limits. **onsemi** should be consulted on applications involving pulsed or low−duty−cycle operations.

THERMAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

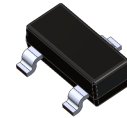| Characteristic	Symbol	Value	Unit
Power Dissipation	P_D	350	mW
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	357	°C/W

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Max	Unit
Breakdown Voltage	B_V	I_R = 100 μA	200	–	V
Forward Voltage	V_F	I_F = 10 mA	–	800	mV
		I_F = 50 mA	760	920	mV
		I_F = 200 mA	–	1.0	V
		I_F = 300 mA	–	1.1	V
Reverse Current	I_R	V_R = 120 V	–	40	nA
		V_R = 175 V	–	100	nA
Total Capacitance	C_T	V_R = 0, f = 1.0 MHz	–	2.0	pF
Reverse Recovery Time	t_{rr}	$I_F = I_R$ = 30 mA, I_{RR} = 3.0 mA, R_L = 100 Ω	–	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
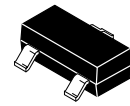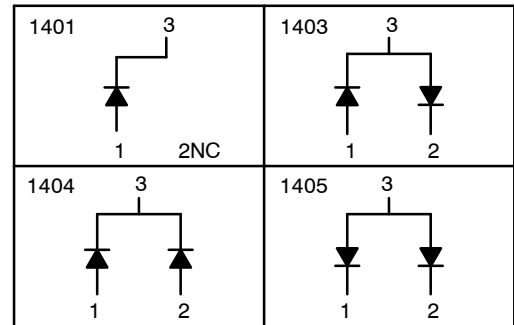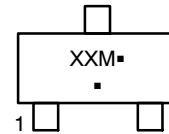
CONNECTION DIAGRAMS

MARKING DIAGRAM

XX = Specific Device Code
      XX = 29/32/33/34
M   = Date Code
▪   = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MMBD1401	SOT−23 (Pb−Free)	3000 / Tape & Reel
MMBD1403	SOT−23 (Pb−Free)	3000 / Tape & Reel
MMBD1404	SOT−23 (Pb−Free)	3000 / Tape & Reel
MMBD1405	SOT−23 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

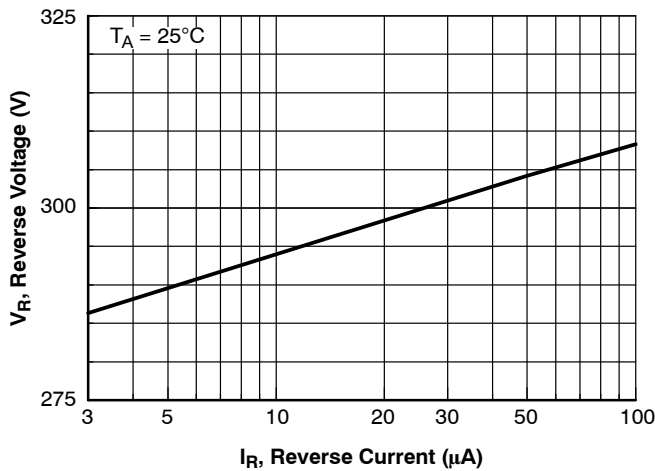# MMBD1401, MMBD1403, MMBD1404, MMBD1405

TYPICAL CHARACTERISTICS

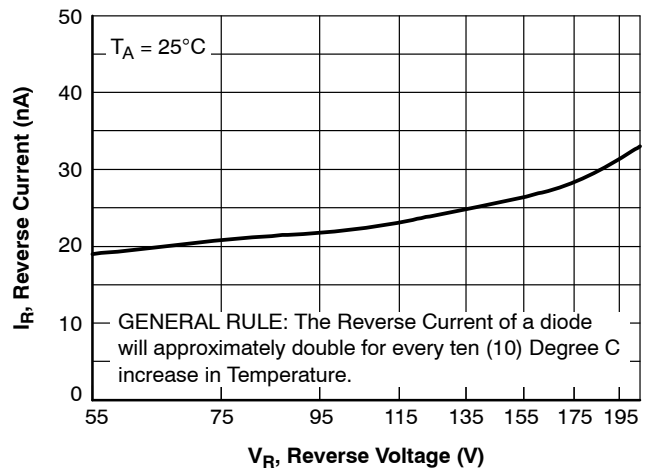Figure 1. Reverse Voltage vs. Reverse Current
B_V – 1.0 to 100 μA
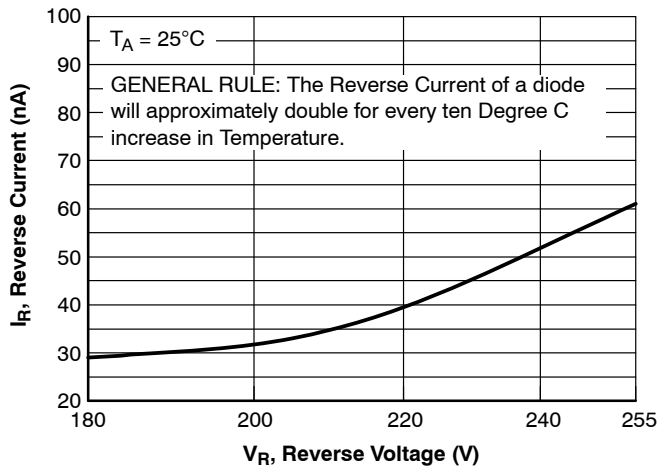
Figure 2. Reverse Current vs. Reverse Voltage
I_R – 55 to 205 V

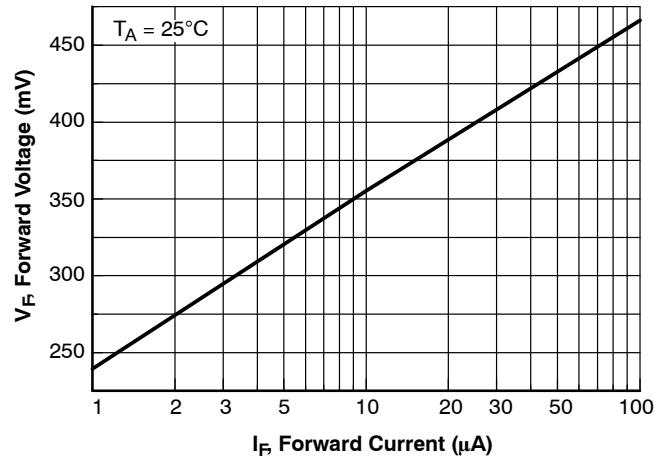Figure 3. Reverse Current vs. Reverse Voltage
I_R – 180 to 255 V

Figure 4. Forward Voltage vs. Forward Current
V_F – 1.0 to 100 μA

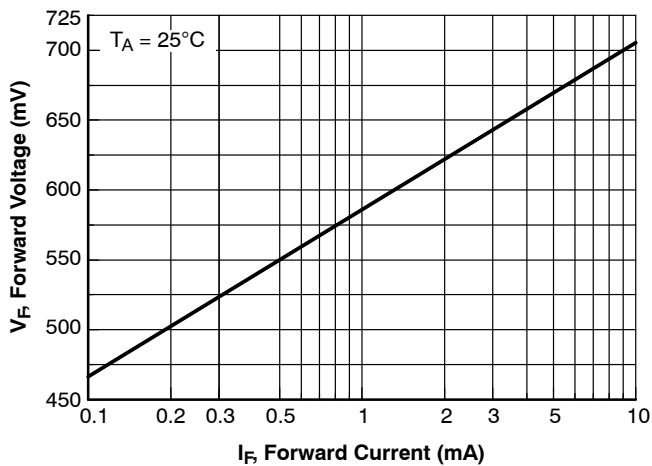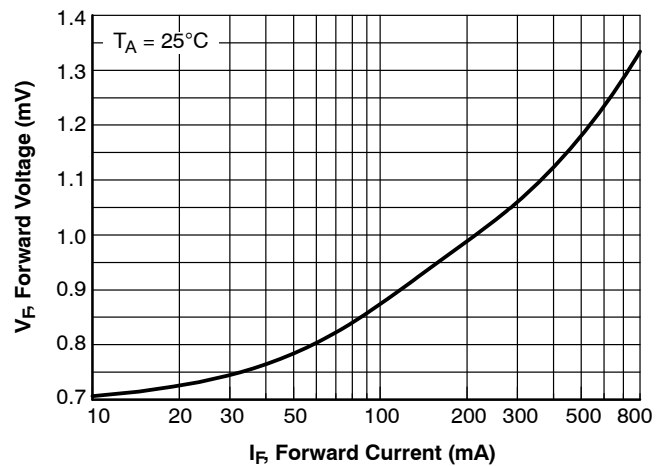Figure 5. Forward Voltage vs. Forward Current
V_F – 0.1 to 10 mA

Figure 6. Forward Voltage vs. Forward Current
V_F – 10 to 800 mA

TYPICAL CHARACTERISTICS (Continued)
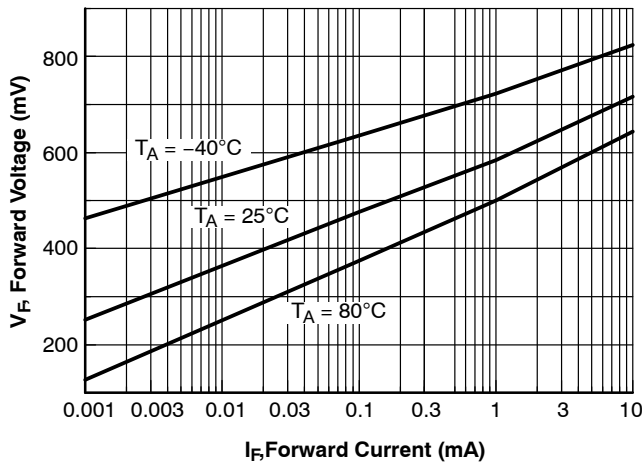
Figure 7. Forward Voltage vs. Ambient Temperature, V_F – 1.0 μA – 10 mA (–40 to +80°C)
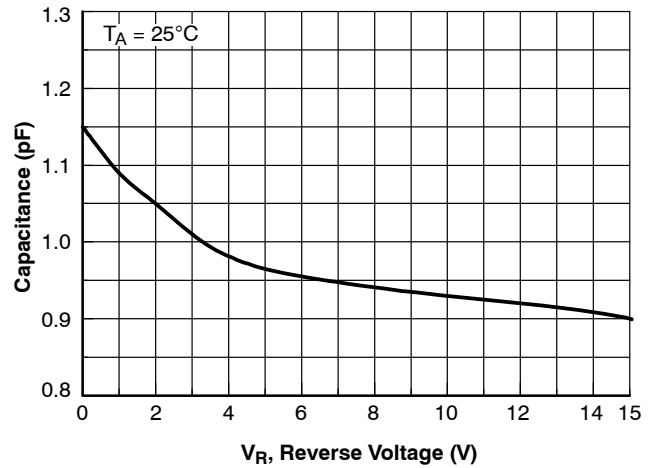
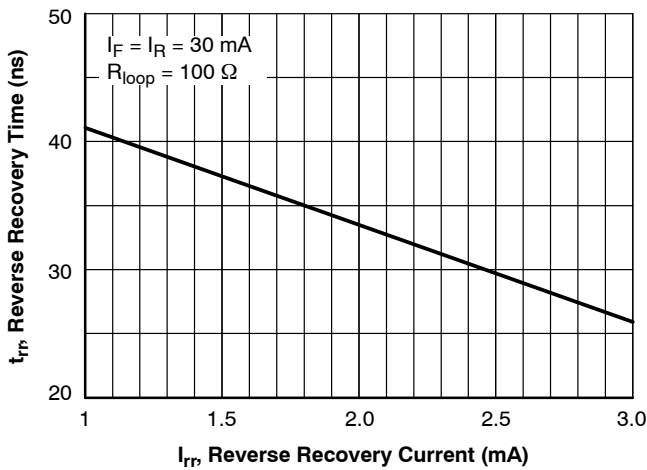**Figure 8. Capacitance vs. Reverse Voltage**

Figure 9. Reverse Recovery Time vs. Reverse Recovery Current (I_{rr})
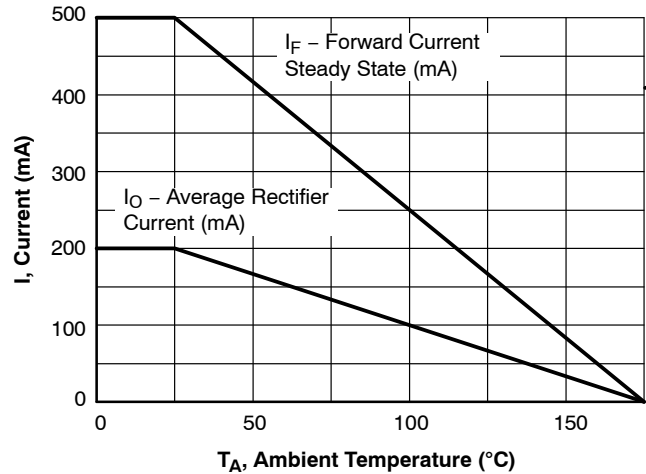

Figure 10. Average Rectified Current (I_O) and Forward Current (I_F) vs. Ambient Temperature (T_A)
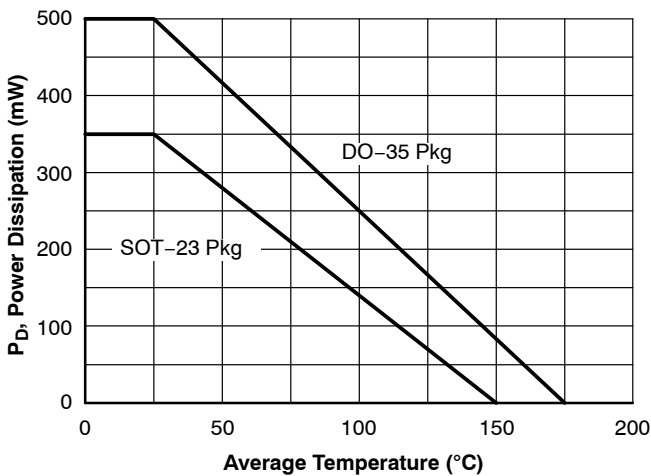

Figure 11. Power Derating Curve

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

SCALE 4:1

TOP VIEW

3X b

e

DETAIL "A"
Scale 3:1

0.25

L

L1

SIDE VIEW

A

A1

END VIEW

DETAIL "A"

c

T

SEATING PLANE

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
H_E	2.10	2.40	2.64
T	0°	---	10°

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*

XXXM▪
▪

1

XXX = Specific Device Code
M   = Date Code
▪   = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

2.90

3X 0.95

3X 0.56

0.95

PITCH

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

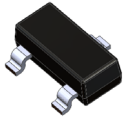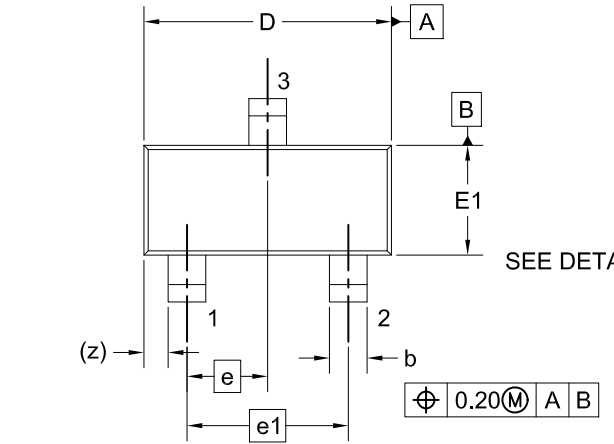| **DOCUMENT NUMBER:**	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT−23 (TO−236) 2.90x1.30x1.00 1.90P		**PAGE 1 OF 2**

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
    2. EMITTER
    3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
    2. BASE
    3. COLLECTOR

STYLE 8:
PIN 1. ANODE
    2. NO CONNECTION
    3. CATHODE

STYLE 9:
PIN 1. ANODE
    2. ANODE
    3. CATHODE

STYLE 10:
PIN 1. DRAIN
    2. SOURCE
    3. GATE

STYLE 11:
PIN 1. ANODE
    2. CATHODE
    3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
    2. CATHODE
    3. ANODE

STYLE 13:
PIN 1. SOURCE
    2. DRAIN
    3. GATE

STYLE 14:
PIN 1. CATHODE
    2. GATE
    3. ANODE

STYLE 15:
PIN 1. GATE
    2. CATHODE
    3. ANODE

STYLE 16:
PIN 1. ANODE
    2. CATHODE
    3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
    2. ANODE
    3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
    2. CATHODE
    3. ANODE

STYLE 19:
PIN 1. CATHODE
    2. ANODE
    3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
    2. ANODE
    3. GATE

STYLE 21:
PIN 1. GATE
    2. SOURCE
    3. DRAIN

STYLE 22:
PIN 1. RETURN
    2. OUTPUT
    3. INPUT

STYLE 23:
PIN 1. ANODE
    2. ANODE
    3. CATHODE

STYLE 24:
PIN 1. GATE
    2. DRAIN
    3. SOURCE

STYLE 25:
PIN 1. ANODE
    2. CATHODE
    3. GATE

STYLE 26:
PIN 1. CATHODE
    2. ANODE
    3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
    2. CATHODE
    3. CATHODE

STYLE 28:
PIN 1. ANODE
    2. ANODE
    3. ANODE

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DESCRIPTION:	SOT−23 (TO−236) 2.90x1.30x1.00 1.90P		**PAGE 2 OF 2**

SOT−23
CASE 318BM
ISSUE A

DATE 01 SEP 2021
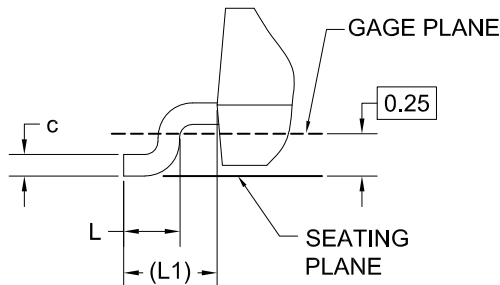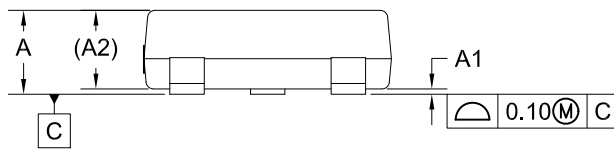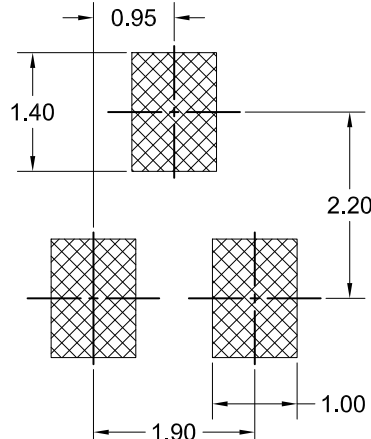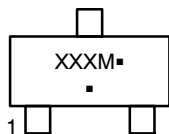
NOTES: UNLESS OTHERWISE SPECIFIED

A) REFERENCE JEDEC REGISTRATION
   TO-236, VARIATION AB, ISSUE H.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS ARE INCLUSIVE OF BURRS,
   MOLD FLASH AND TIE BAR EXTRUSIONS.
D) DIMENSIONING AND TOLERANCING PER
   ASME Y14.5M - 2009.

SEE DETAIL A

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.20
A1	0.00	0.05	0.10
A2	0.93 REF		
b	0.37	0.44	0.60
c	0.08	0.15	0.23
D	2.72	2.92	3.12
E	2.10	2.40	2.70
E1	1.15	1.30	1.50
e	0.95 BSC		
e1	1.90 BSC		
L	0.20	---	---
L1	0.55 REF		
z	0.29 REF		

⊕ 0.20 Ⓜ A B

▽ 0.10 Ⓜ C

GAGE PLANE

0.25

SEATING PLANE

DETAIL A
SCALE: 2X

0.95

1.40

2.20

1.00

1.90

LAND PATTERN RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*

XXXM■
■

1

XXX = Specific Device Code
M = Date Code
■ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOT−23	PAGE 1 OF 1

ADDITIONAL INFORMATION

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